

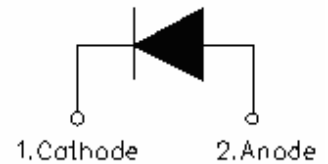
## SBRF1060 SCHOTTKY RECTIFIER

### Applications:

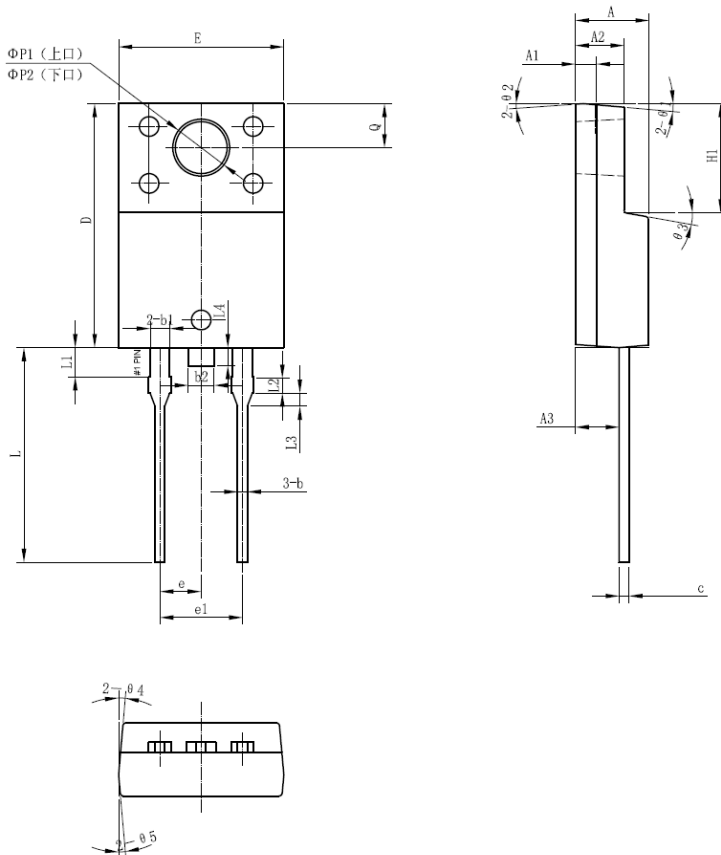
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

### Features:

- 150 °C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



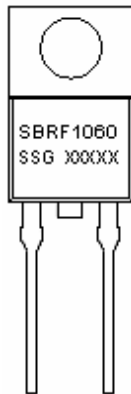
### Mechanical Dimensions: In mm



SYMBOL	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
c	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e	-	2.55	-
e1	-	5.10	-
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
L4	-	1.10	1.50
ΦP1(上孔)	3.30	3.50	3.70
ΦP2(下孔)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

### ITO-220AC(HD)

**Marking Diagram:**



Where XXXXX is YYWWL

SBR = Device Type  
 F = Package type  
 10 = Forward Current (10A)  
 60 = Reverse Voltage (60V)  
 SSG = SSG  
 YY = Year  
 WW = Week  
 L = Lot Number

**Cautions:** Molding resin  
 Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
SBRF1060	ITO-220AC (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	60	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 135^\circ\text{C}$ , rectangular wave form	10	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	$I_{FSM}$	8.3 ms, half Sine pulse	130	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop *	$V_{F1}$	@ 10A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.80	V
	$V_{F2}$	@ 10A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.70	V
Max. Reverse Current *	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.0	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	30	mA
Max. Junction Capacitance	$C_T$	@ $V_R = 4\text{V}$ , $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	300	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ $\mu\text{s}$

\* Pulse Width < 300 $\mu\text{s}$ , Duty Cycle <2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	$T_J$	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	5.0	$^\circ\text{C/W}$
Typical Thermal Resistance, Case to Heat Sink	$R_{\theta CS}$	Mouting surface, smooth and greased	0.50	$^\circ\text{C/W}$
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC			

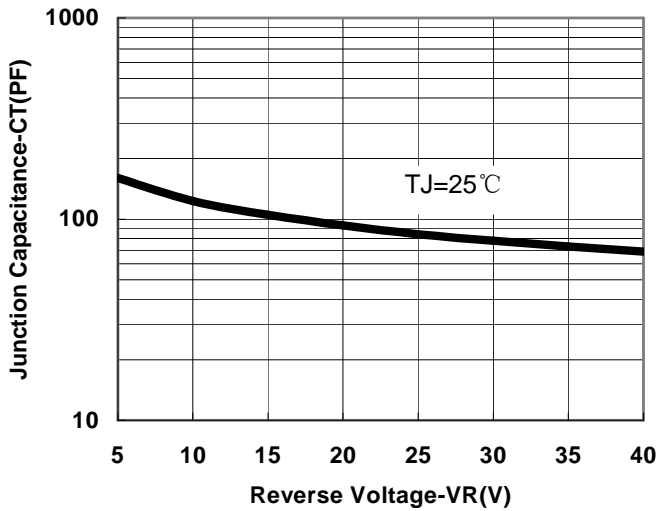


Fig.1-Typical Junction Capacitance

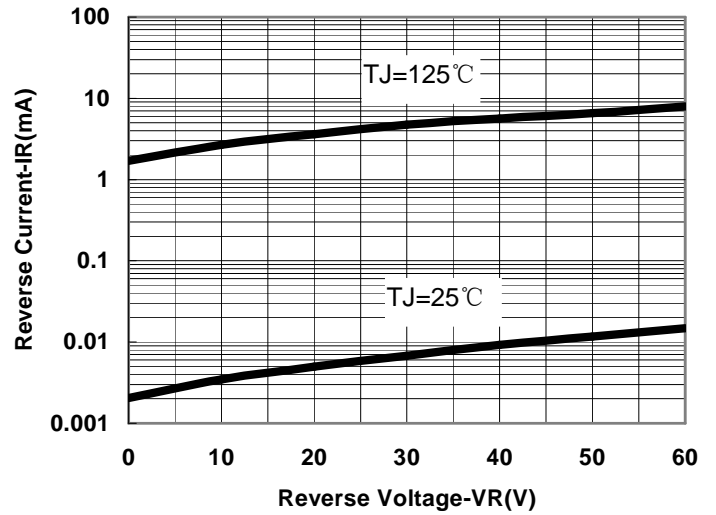


Fig.2-Typical Reverse Characteristics

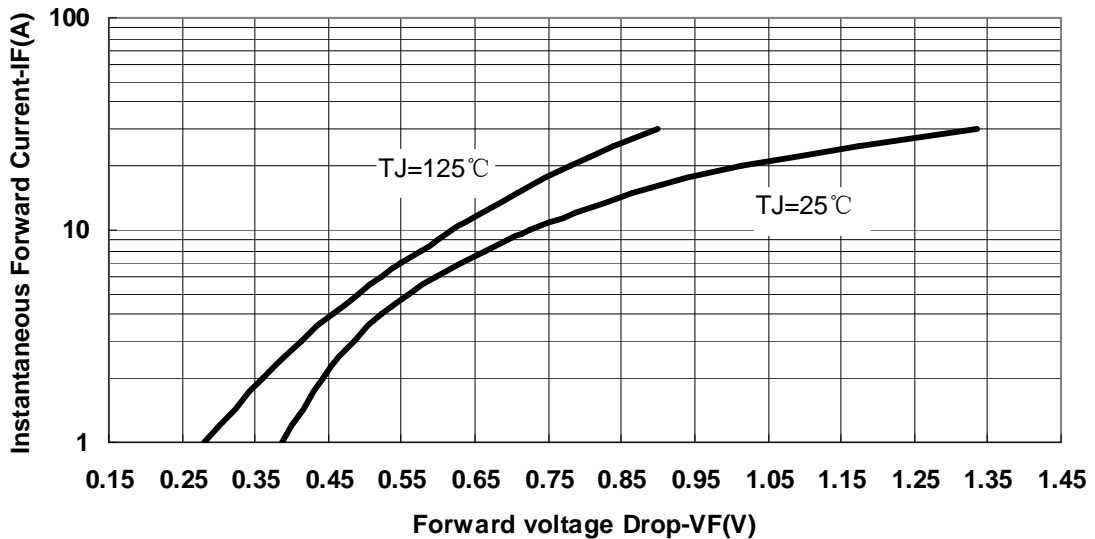


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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